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MCLEAN, VIRGINIA

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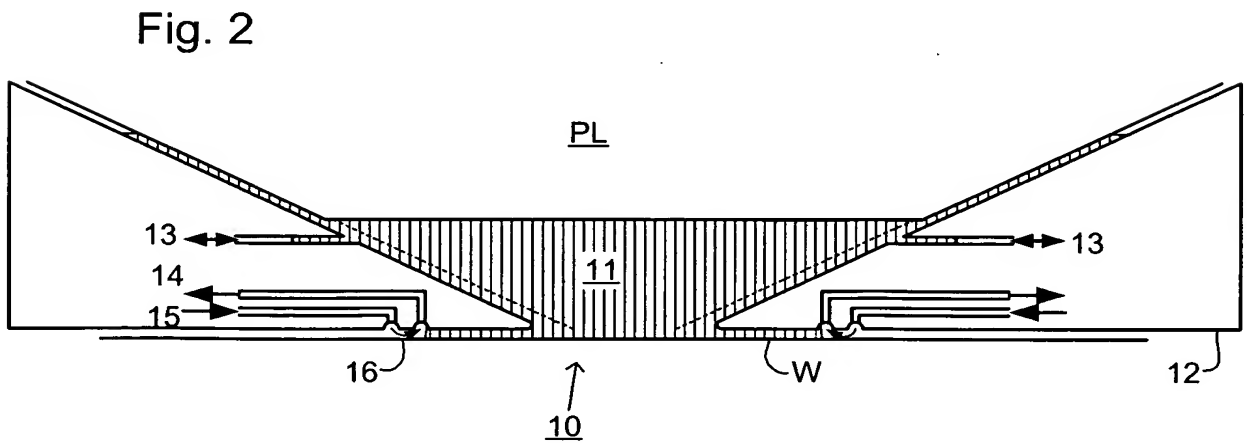
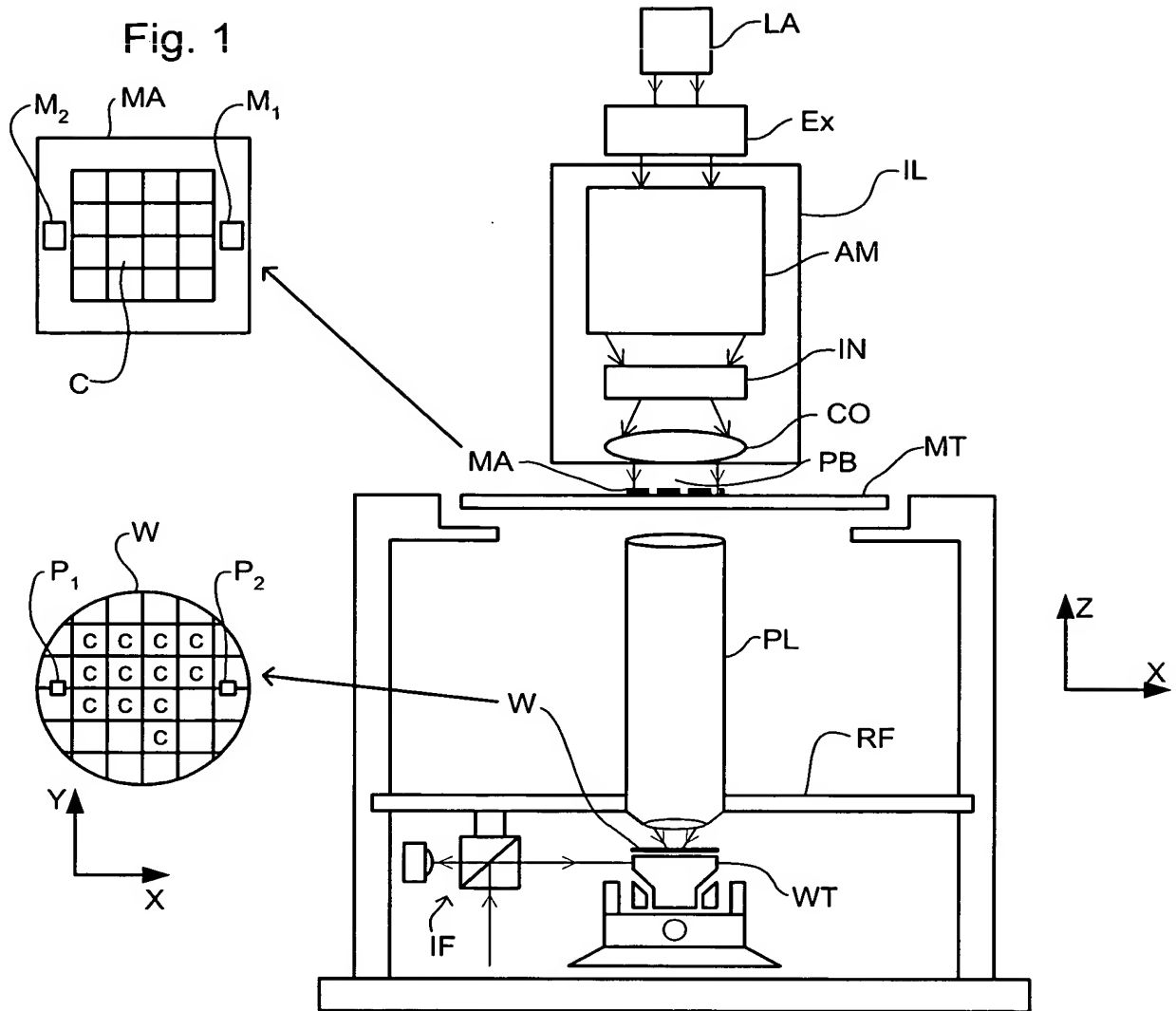


Fig. 3

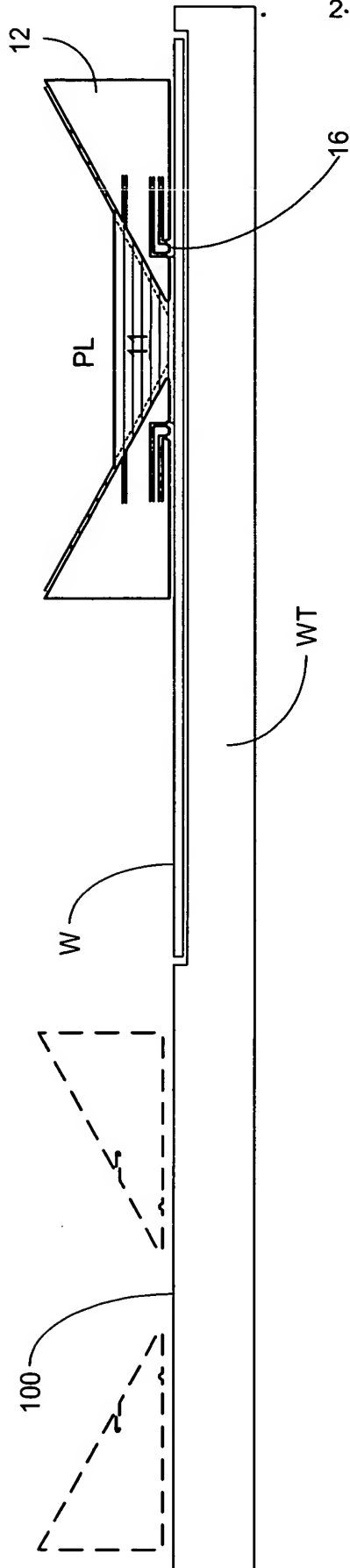
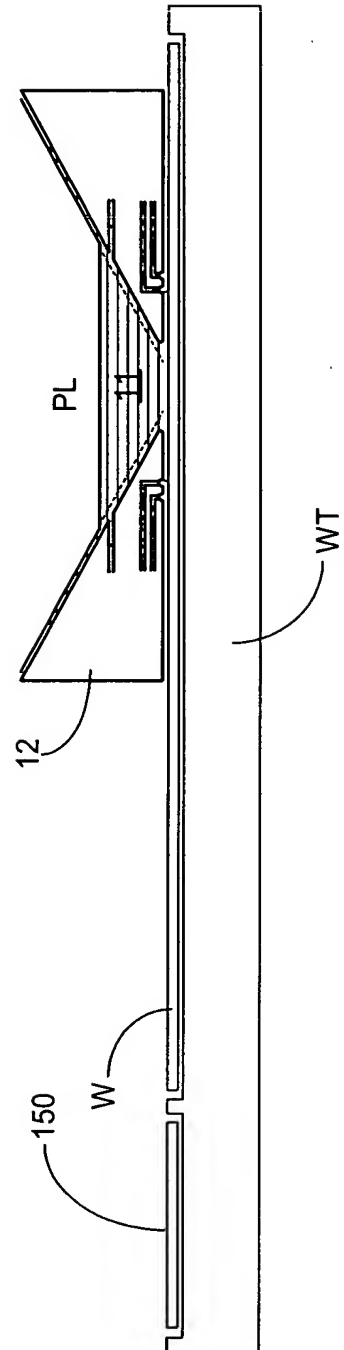


Fig. 4



A cross-sectional view of a semiconductor device. A central channel region is labeled **11**. On either side of the channel are side regions labeled **12**. A layer labeled **PL** is positioned above the channel and side regions. Below the channel, a layer labeled **150** is shown, with a sub-layer labeled **170** underneath it. The entire structure is supported by a substrate labeled **WT**. On the left and right sides, there are structures labeled **160** and **17** respectively, which appear to be part of a larger assembly or contact structure.

Fig. 7

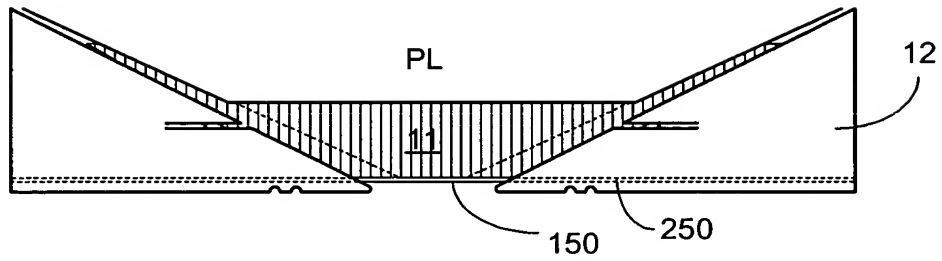
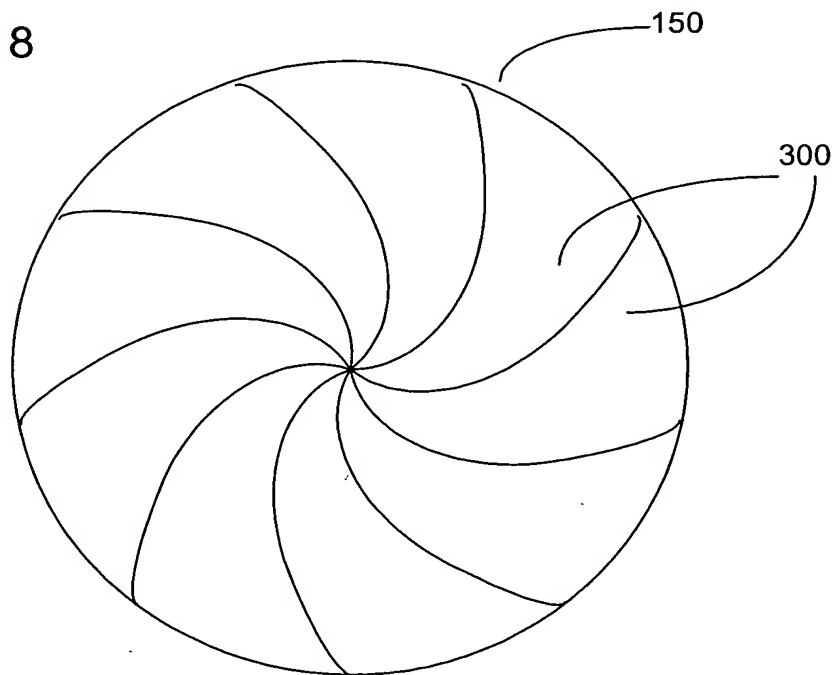


Fig. 8



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Fig. 9

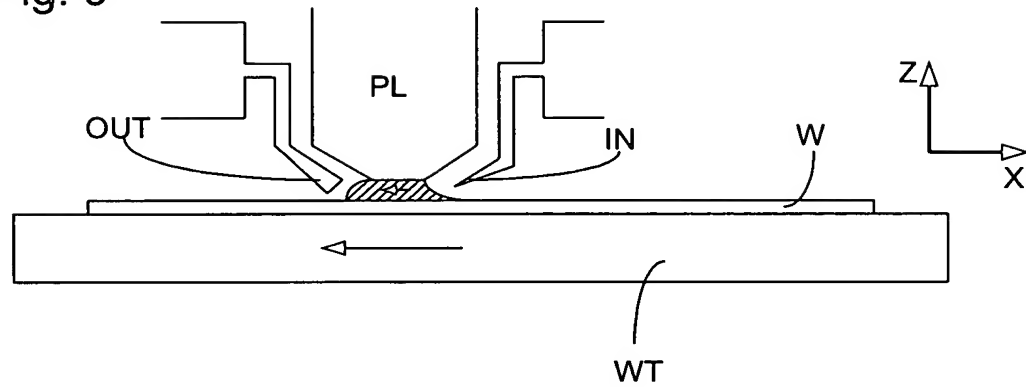


Fig. 10

